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(54) **NEGATIVE RESIST PATTERN FORMING METHOD, DEVELOPER AND NEGATIVE CHEMICAL-AMPLIFICATION RESIST COMPOSITION USED THEREFOR, AND RESIST PATTERN**

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See application file for complete search history.

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(57) **ABSTRACT**

A resist pattern forming method including in the following order, (1) a step of forming a film by using a negative chemical-amplification resist composition capable of undergoing negative conversion by a crosslinking reaction, (2) a step of exposing the film, and (4) a step of developing the exposed film by using a developer containing an organic solvent; a developer and a negative chemical-amplification resist composition used therefor; and a resist pattern formed by the pattern forming method.

**16 Claims, No Drawings**